RFIC Design and Testing for Wireless Communications

A PragaTI (TI India Technical University) Course July 18, 21, 22, 2008

Lecture 9: Frequency synthesizer design II (VCO)

By

Vishwani D. Agrawal Fa Foster Dai

200 Broun Hall, Auburn University Auburn, AL 36849-5201, USA

RFIC Design and Testing for Wireless Communications

Topics

Monday, July 21, 2008

9:00 - 10:30	Introduction - Semiconductor history, RF characteristics
11:00 – 12:30	Basic Concepts - Linearity, noise figure, dynamic range
2:00 - 3:30	RF front-end design - LNA, mixer
4:00 - 5:30	Frequency synthesizer design I (PLL)

Tuesday, July 22, 2008

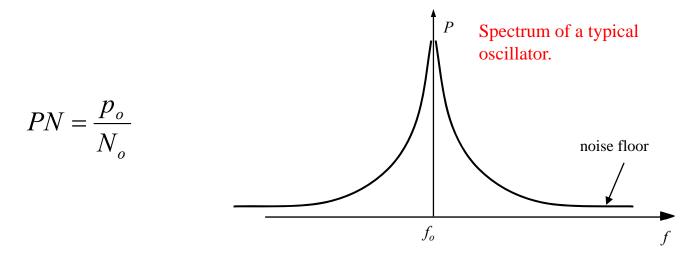
9:00 – 10:30	Frequency synthesizer design II	(VCO)
11:00 – 12:30	RFIC design for wireless communic	cations
2:00 - 3:30	Analog and mixed signal testing	

Phase Noise Specification of Oscillators

Example of oscillator periodic waveforms



• Phase noise. We desire accurate periodicity with all signal power concentrated in one discrete oscillator frequency → an impulse function in frequency domain. However, all real oscillators have less than perfect spectral purity and thus they develop "skirts". Power in the skirts is evidence of phase noise, Phase noise is any noise that charges the frequency or phase of the oscillator waveform. Phase noise is given by:

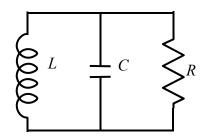


• Where *Po* is the power in the tone at the frequency of oscillation and No is the noise power spectral density at some specified offset from the carrier. Phase noise is usually specified in *dBc/Hz*, meaning noise a 1-Hz bandwidth measured in decibels with respect to the carrier.

LC Resonator – Core of Oscillators

• If $i(t) = I_{pulse} \delta(t)$ is applied to a parallel resonator, the time domain response of the system can be found as:

$$v_{out} = \frac{\sqrt{2}I_{pulse}e^{\frac{-t}{2RC}}}{C}\cos\left(\sqrt{\frac{1}{LC} - \frac{1}{4R^2C^2}} \bullet t\right)$$

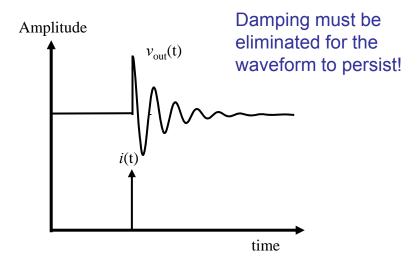


Oscillation frequency

$$\omega_{OSC} = \sqrt{\frac{1}{LC} - \frac{1}{4R^2C^2}}$$

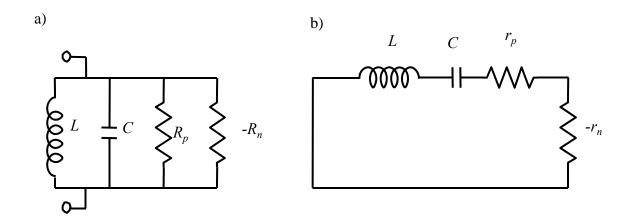
• In most oscillators, $|R| >> \sqrt{L/C}$

$$\omega_{OSC} = \sqrt{\frac{1}{LC}}$$

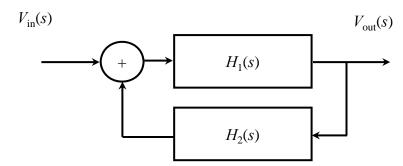


Damped LC resonator with current step applied.

Adding Negative Resistance Trough Feedback to Resonator



The addition of negative resistance to the circuit to overcome losses in a) a parallel resonator or b) a series resonator.



Linear model of an oscillator as a feedback control system.

Barkhausen Criterion

Closed loop gain

$$\frac{V_{out}(s)}{V_{in}(s)} = \frac{H_1(s)}{1 - H_1(s)H_2(s)}$$

Condition for oscillation: denominator approaches zero. → To find the closed-loop poles

$$1 - H_1(s)H_2(s) = 0$$

• For sustained oscillation at constant amplitude, the pole must be on the $j\omega$ axis. For the open-loop analysis

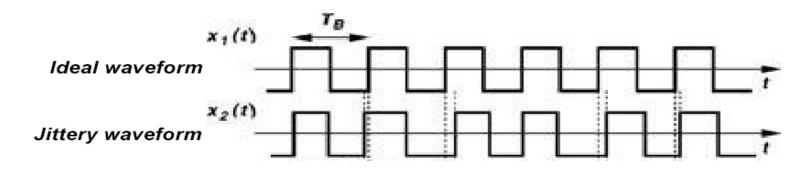
$$H_1(j\omega)H_2(j\omega) = 1$$

positive feedback with gain larger than or equal to 1.

• Barkhausen criterion, which states that for sustained oscillation at constant amplitude, the gain around the loop is 1 and the phase around the loop is 0 or some multiple of 2π .

$$|H_1(j\omega)|H_2(j\omega)| = 1$$
 $\angle H_1(j\omega)H_2(j\omega) = 2n\pi$

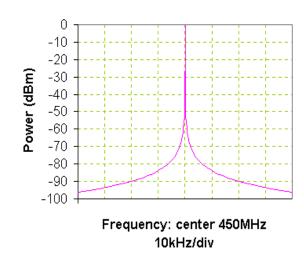
VCO Output Spectral Purity



Noise in one sideband in a 1Hz bandwidth:

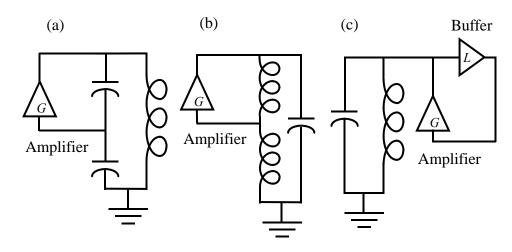
 $L_{total}(\Delta w) = \underline{noise power in 1Hz BW at w_o + \Delta w}$ Carrier power

Units: dBc/Hz

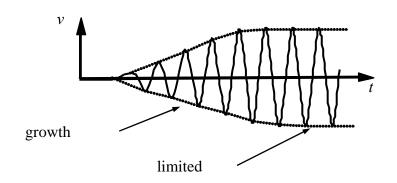


VCO Output Spectrum

Popular Implementation of Feedback to Resonator



Resonators with feedback. (a) Colpitts Oscillator. (b) Hartley Oscillator (not suitable for IC). (c) $-G_m$ oscillator.

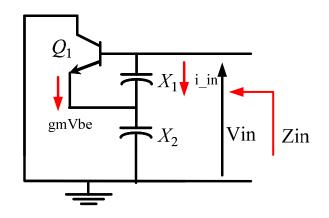


Waveform of an LC resonator with losses compensated. The oscillation grows until a practical constraint limits the amplitude.

Negative Resistance of Colpitts Amplifier

$$v_{in} = i_{in}(jX_1 + jX_2) + g_m v_{be}(jX_2)$$
 Negative Impedance, if X and X₂ are the same type

Negative Impedance, if X₁



$$Z_{in} = \frac{v_{in}}{i_{in}} = -g_m X_1 X_2 + j(X_1 + X_2)$$

$$Z_{in} = \frac{v_{in}}{i_{in}} = -g_m X_1 X_2 + j(X_1 + X_2)$$

$$Z_{in} = -\frac{g_m}{\omega^2 C_1 C_2} + \frac{1}{j\omega C_1} + \frac{1}{j\omega C_2}$$

To start the oscillation,

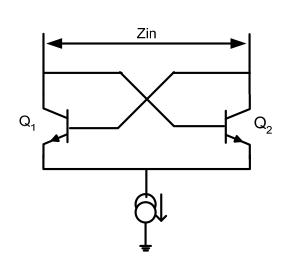
$$-g_m X_1 X_2 > R_L$$
$$g_m > R_L \omega^2 C_1 C_2$$

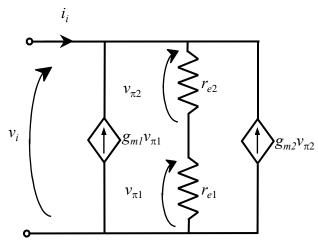
Load reactance needs to equal $-j(X_1+X_2) \rightarrow$ add an inductor

Oscillation frequency

$$f_{osc} = \frac{1}{2\pi} \left[\frac{1}{L_3} \left(\frac{1}{C_1} + \frac{1}{C_2} \right) \right]^{\frac{1}{2}}$$

Negative Resistance of –Gm Oscillator





$$i_i = \frac{v_i}{r_{e1} + r_{e2}} = -g_{m1}v_{\pi 1} - g_{m2}v_{\pi 2}$$

- Both transistors are biased identically, $Z_i = \frac{-2}{g_m}$
- Condition for oscillation is that

$$g_m > \frac{2}{R_p}$$

where Rp is the equivalent parallel resistance of the resonator.

VCO Mathematical Model

Output frequency of an ideal VCO:

$$W_{out} = W_{FR} + K_{vco}V_c$$

Sinusoidal output:
$$y(t) = A \cos(w_{FR}t + K_{vco} \int_{-\infty}^{t} V_C)$$

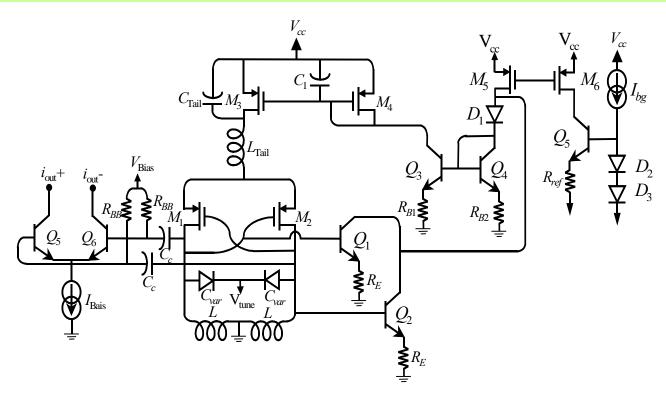
Open loop Q:
$$Q = \frac{w_0}{2} \left| \frac{d\phi}{dw} \right|$$

w₀ is the center frequency

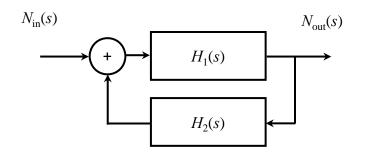
 ϕ is the phase of open loop transfer function

PMOS VCO with Automatic Amplitude Control

- Large V_{tune} range (almost from 0V ~ Vcc V).
- Tank can be connected to ground rather than DC → lower phase noise and diodes can be connected in the proper polarity without additional biasing.
- PMOS transistors can be operated into saturation without affecting the VCO noise performance → higher output swing than bipolar VCO.
- High phase noise below 100kHz offset (due to high flicker noise) → can be tolerated by wider loop bandwidth (>100kHz).



Linear or Addictive Phase Noise -- Leeson's Formula



Oscillator Phase Noise $\Phi_n(t)$

$$V_{OSC} = A\cos[\omega_0 t + \phi_n(t)]$$

Noise close loop transfer function

$$\frac{N_{out}(s)}{N_{in}(s)} = \frac{H_1(s)}{1 - H(s)}$$

Open loop transfer function $H(s)=H_1(s)H_2(s)$

$$H(j\omega) \approx H(j\omega_0) + \Delta\omega \frac{dH}{d\omega}$$

Oscillation conditions
$$H(j\omega_0) = 1 \longrightarrow H_1(j\omega_0) = H_1$$

Noise power

$$\left| \frac{N_{out}(s)}{N_{in}(s)} \right|^2 = \frac{\left| H_1 \right|^2}{\left(\Delta \omega \right)^2 \left| \frac{dH}{d\omega} \right|^2}$$

$$H(\omega) = |H|e^{j\phi} \qquad \frac{dH}{d\omega} = \frac{d|H|}{d\omega}e^{j\phi} + |H|je^{j\phi} \frac{d\phi}{d\omega}$$
ignorable dominant
$$\left|\frac{dH}{d\omega}\right|^{2} = \left|\frac{d|H|}{d\omega}\right|^{2} + |H|^{2} \left|\frac{d\phi}{d\omega}\right|^{2}$$
Orthogonal

• At resonance, the phase changes much faster than magnitude, and |H|=1 near resonance. → ignore amplitude noise and AM to PM conversion as well.

$$\left| \frac{dH}{d\omega} \right|^{2} = \left| \frac{d\phi}{d\omega} \right|^{2} \longrightarrow \left| \frac{N_{out}(s)}{N_{in}(s)} \right|^{2} = \frac{\left| H_{1} \right|^{2}}{\left(\Delta \omega \right)^{2} \left| \frac{d\phi}{d\omega} \right|^{2}}$$

$$Q = \frac{\omega_{0}}{2} \left| \frac{d\phi}{d\omega} \right| \longrightarrow \left| \frac{N_{out}(s)}{N_{in}(s)} \right|^{2} = \frac{\left| H_{1} \right|^{2} \omega_{0}^{2}}{4Q^{2} \left(\Delta \omega \right)^{2}}$$

• If feedback path is unity, then $H_1=H$, and since |H|=1 near resonance

$$\left|\frac{N_{out}(s)}{N_{in}(s)}\right|^{2} = \frac{\omega_{0}^{2}}{4Q^{2}(\Delta\omega)^{2}}$$

• Phase noise is quoted as an absolute noise referred to the carrier power

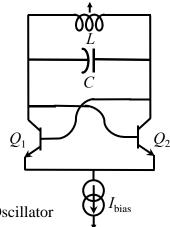
$$PN = \frac{\left|N_{out}(s)\right|^2}{2P_S} = \left(\frac{\left|H_1\right|\omega_0}{\left(2Q\Delta\omega\right)}\right)^2 \left(\frac{\left|N_{in}(s)\right|}{2P_S}\right)$$

- Ps is the signal power at active device input.
- If the transistor and bias were noiseless, then the only noise present would be due to the resonator losses. The transistors and the bias will add noise to the minimum noise of

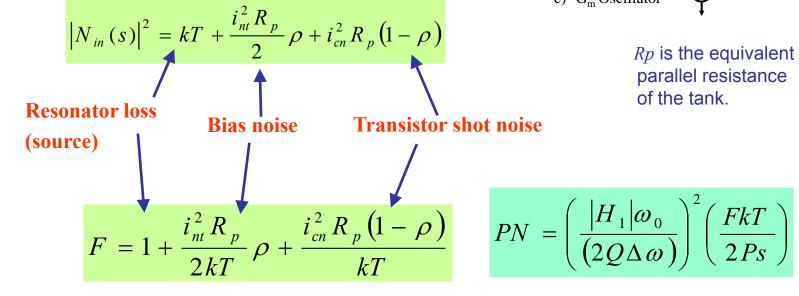
$$\left|N_{in}\left(s\right)\right|^{2} = kT$$

Active Device noise:

- If ρ is the fraction of cycle for which the transistors are completely switched, in tis the noise current injected into the oscillator from the bias during this time.
- During transitions $(1-\rho)$, the transistors act like an amplifier, and collector shot noise i_{cn} usually dominates.



c) -G_m Oscillator



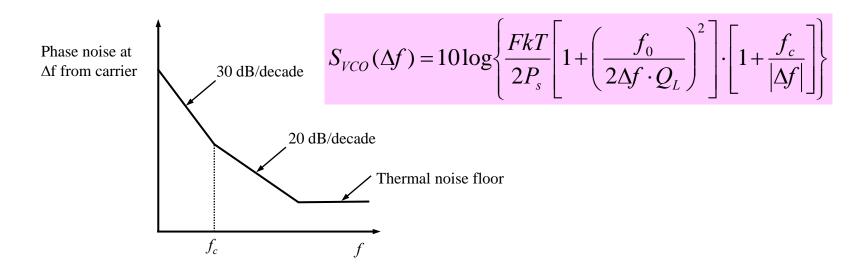
Rp is the equivalent parallel resistance of the tank.

$$PN = \left(\frac{|H_1|\omega_0}{(2Q\Delta\omega)}\right)^2 \left(\frac{FkT}{2Ps}\right)$$

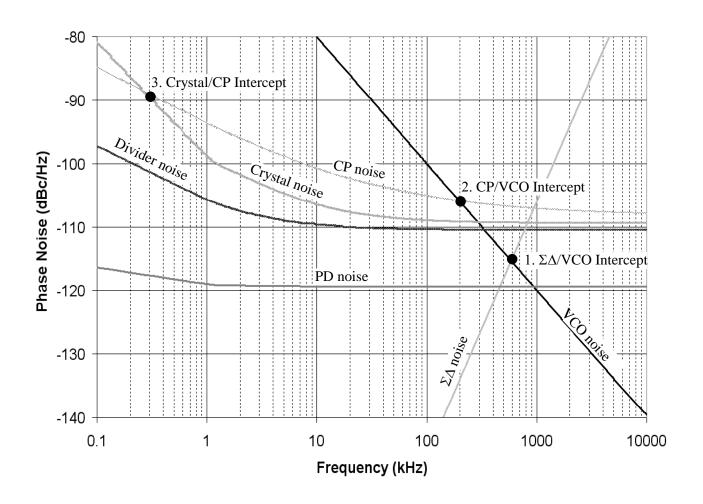
• It has been assumed that flicker noise is insignificant at the frequencies of interest. This may not be the case for CMOS designs. If ωc represents the flicker noise corner where flicker noise and thermal noise are equal, phase noise is given by

$$PN = \left(\frac{|H_1|\omega_0}{(2Q\Delta\omega)}\right)^2 \left(\frac{FkT}{2Ps}\right) \left(1 + \frac{\omega_c}{\Delta\omega}\right)$$

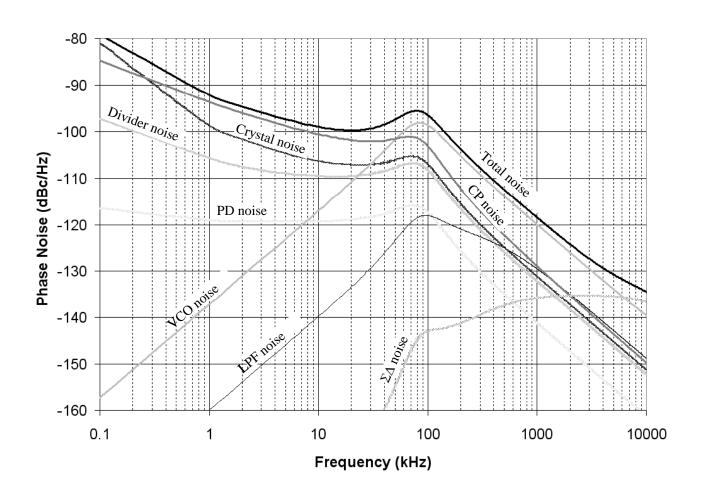
Assuming unity feedback, oscillator output spectrum density



Simulated PLL Phase Noise Sources



Simulated PLL Phase Noise With Loop Effect



Comparison of measured and simulated phase noise

